OptiMOS™2 Power-Transistor

Features

- Dual N-channel, normal level
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Low on-resistance $R_{DS(on)}$
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC[1] for target application
- Ideal for high-frequency switching and synchronous rectification
- 100% avalanche tested
- Halogen-free according to IE61249-2-21

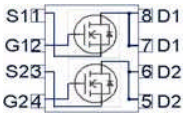
RoHS Halogen-Free

Product Summary

V_{DS}	100	V
$R_{DS(on),max}$	75	mΩ
I_D	13	A

PG-TDSON-8

Type	Package	Marking
BSC750N10ND G	PG-TDSON-8	750N10ND



Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value		Unit
			≤10 secs	steady state	
Continuous drain current	I_D	V_{GS}=10 V, T_C=25 °C	13		A
		V_{GS}=10 V, T_C=100 °C	8.5		
		V_{GS}=10 V, T_A=25 °C[3]	5.0	3.2	
Pulsed drain current[2]	$I_{D,pulse}$	T_C=25 °C	52		
Avalanche energy, single pulse	E_{AS}	I_D=13 A, R_{GS}=25 Ω	17		mJ
Reverse diode dv/dt	dv/dt	I_D=13 A, V_{DS}=80 V, di/dt=100 A/µs, $T_{j,max}$=150 °C	6		kV/µs
Gate source voltage	V_{GS}		±20		V
Power dissipation	P_{tot}	T_C=25 °C	26		W
		T_A=25 °C[3]	3.6	1.5	
Operating and storage temperature	T_j, T_{stg}		-55 ... 150		°C
IEC climatic category; DIN IEC 68-1			55/150/56		

[1] J-STD20 and JESD22

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}	bottom	-	-	4.9	K/W
		top			20	
Thermal resistance, junction - ambient, 6 cm² cooling area[3)]	R_{thJA}	t≤10 s	-	-	35	
		steady state	-	-	85	
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=1 mA	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=12 µA	2	3	4	
Zero gate voltage drain current	I_{DSS}	V_{DS}=100 V, V_{GS}=0 V, T_j=25 °C	-	0.1	1	µA
		V_{DS}=100 V, V_{GS}=0 V, T_j=125 °C	-	10	100	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=13 A	-	62	75	mΩ
Gate resistance	R_G		-	0.8	-	Ω
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=13 A	6.5	13	-	S

[2)] See figure 3

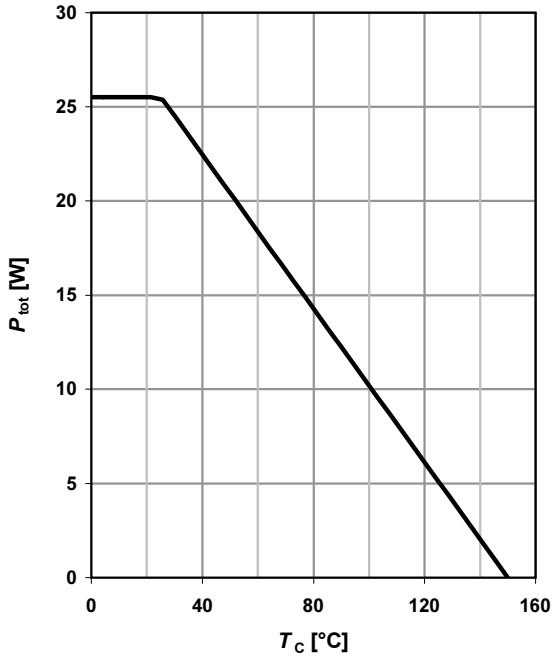
[3)] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air. One transistor active.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=50 V, f=1 MHz	-	540	720	pF
Output capacitance	C_{oss}		-	76	100	
Reverse transfer capacitance	C_{rss}		-	8	12	
Turn-on delay time	$t_{d(on)}$	V_{DD}=50 V, V_{GS}=10 V, I_D=13 A, R_G=2.4 Ω	-	9	13	ns
Rise time	t_r		-	4	6	
Turn-off delay time	$t_{d(off)}$		-	13	18	
Fall time	t_f		-	3	4	
Gate Charge Characteristics[4)]						
Gate to source charge	Q_{gs}	V_{DD}=50 V, I_D=13 A, V_{GS}=0 to 10 V	-	3	4	nC
Gate to drain charge	Q_{gd}		-	2	3	
Switching charge	Q_{sw}		-	4	6	
Gate charge total	Q_g		-	8	11	
Gate plateau voltage	$V_{plateau}$		-	6	-	V
Output charge	Q_{oss}	V_{DD}=50 V, V_{GS}=0 V	-	8	10	
Reverse Diode						
Diode continuous forward current	I_S	T_C=25 °C	-	-	13	A
Diode pulse current	$I_{S,pulse}$		-	-	52	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=13 A, T_j=25 °C	-	1	1.2	V
Reverse recovery time	t_{rr}	V_R=50 V, I_F=I_S, di_F/dt=100 A/µs	-	67		ns
Reverse recovery charge	Q_{rr}		-	114	-	nC

[4)] See figure 16 for gate charge parameter definition

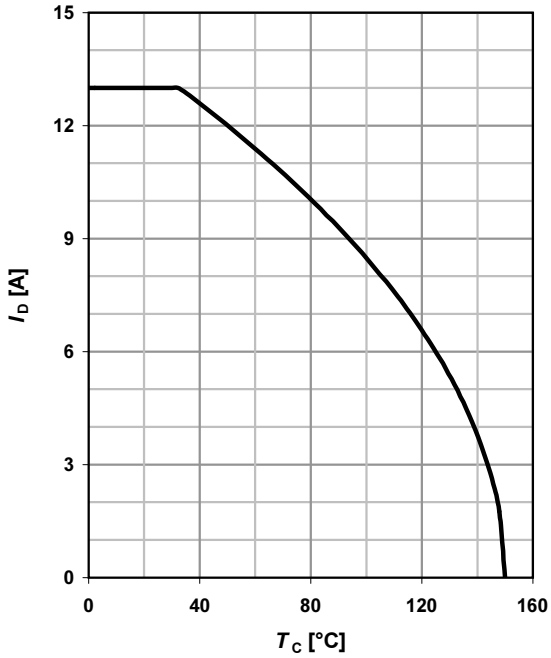
1 Power dissipation

$P_{tot}=f(T_C)$



2 Drain current

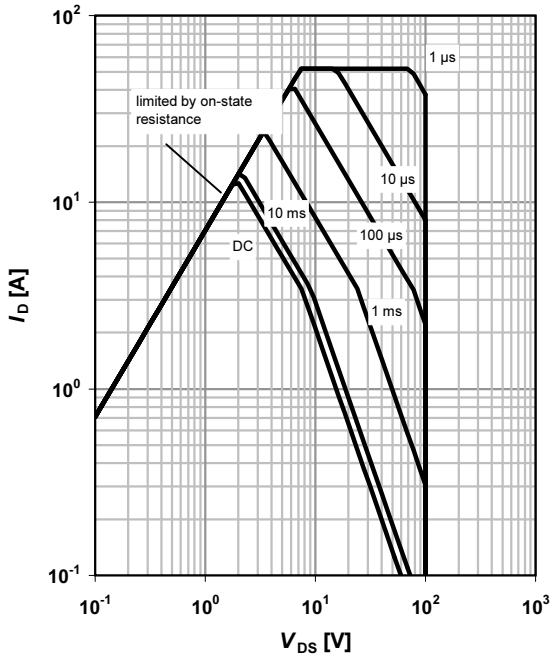
$I_D=f(T_C)$; $V_{GS}\geq 10$ V



3 Safe operating area

$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$

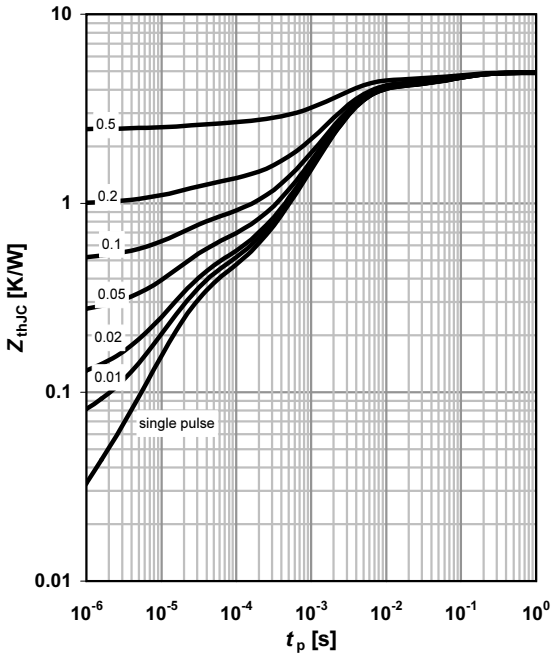
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

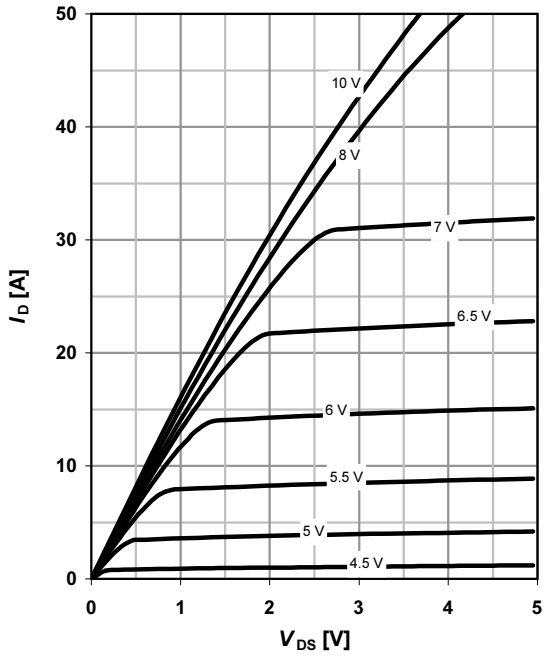
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D=f(V_{DS})$; $T_j=25$ °C

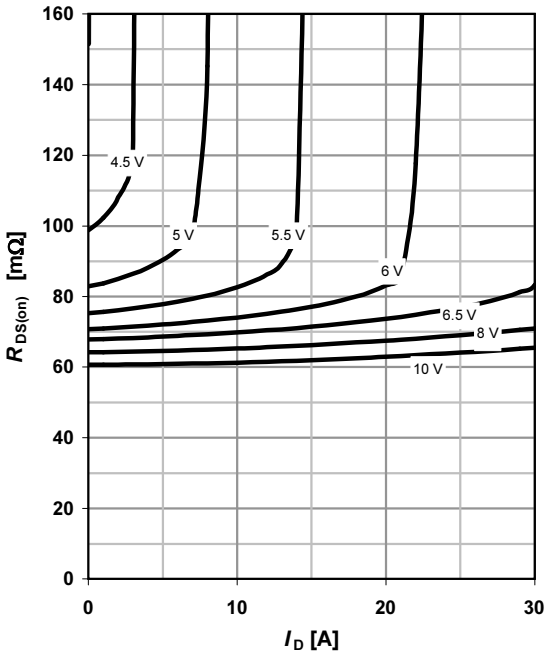
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)}=f(I_D)$; $T_j=25$ °C

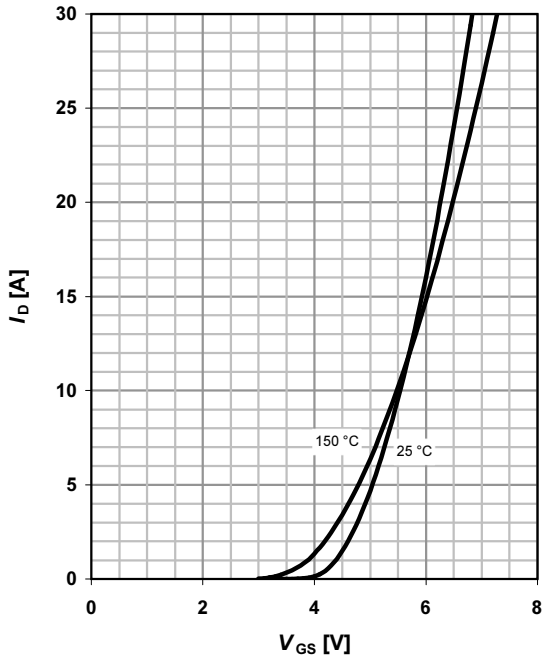
parameter: V_{GS}



7 Typ. transfer characteristics

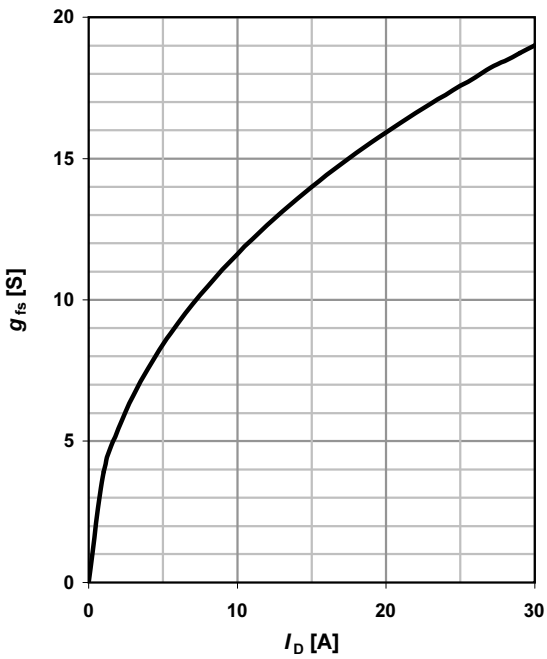
$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$

parameter: T_j



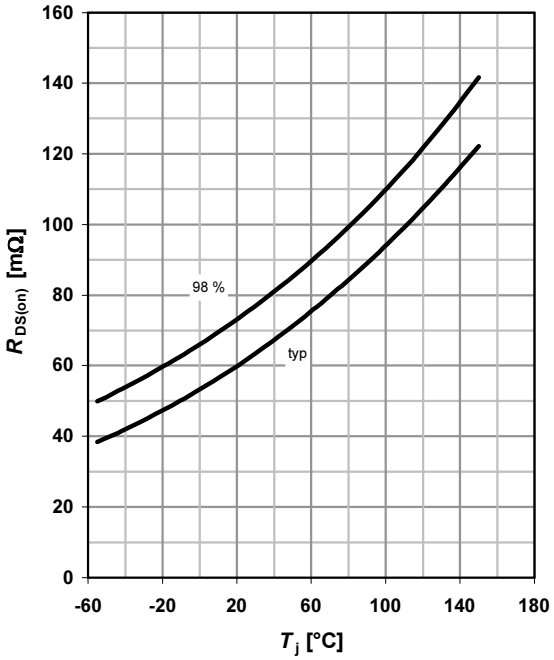
8 Typ. forward transconductance

$g_{fs}=f(I_D)$; $T_j=25$ °C



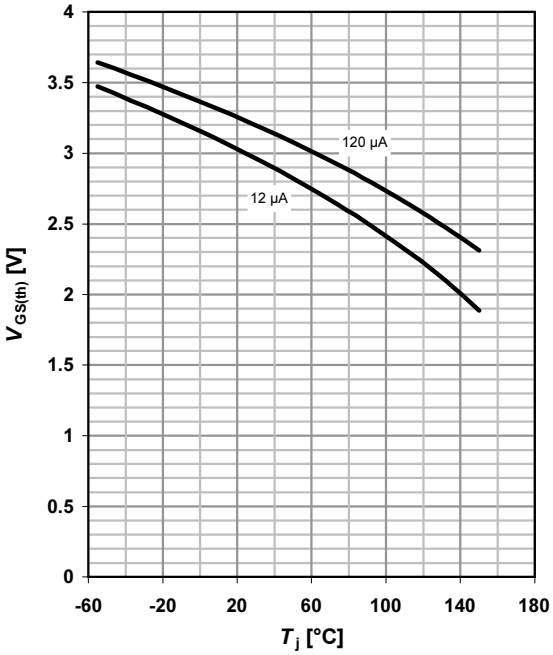
9 Drain-source on-state resistance

$R_{DS(on)}=f(T_j)$; $I_D=13$ A; $V_{GS}=10$ V



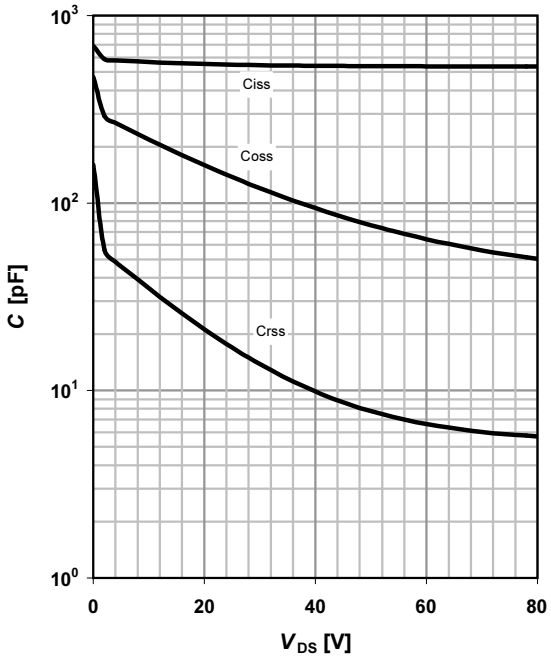
10 Typ. gate threshold voltage

$V_{GS(th)}=f(T_j)$; $V_{GS}=V_{DS}$



11 Typ. capacitances

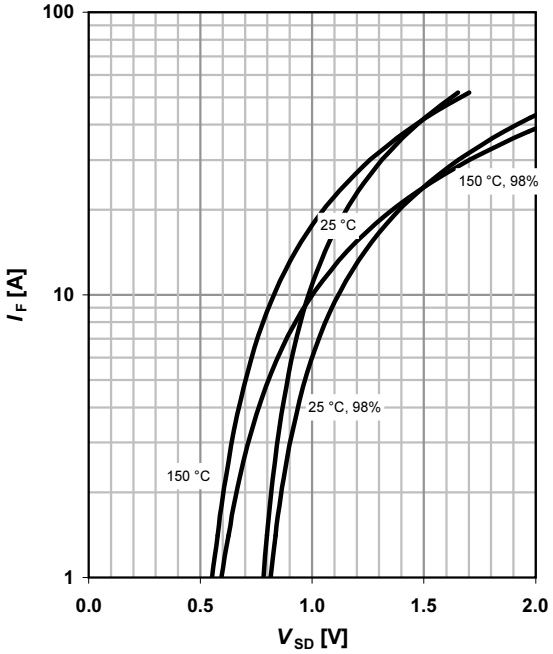
$C=f(V_{DS})$; $V_{GS}=0$ V; $f=1$ MHz



12 Forward characteristics of reverse diode

$I_F=f(V_{SD})$

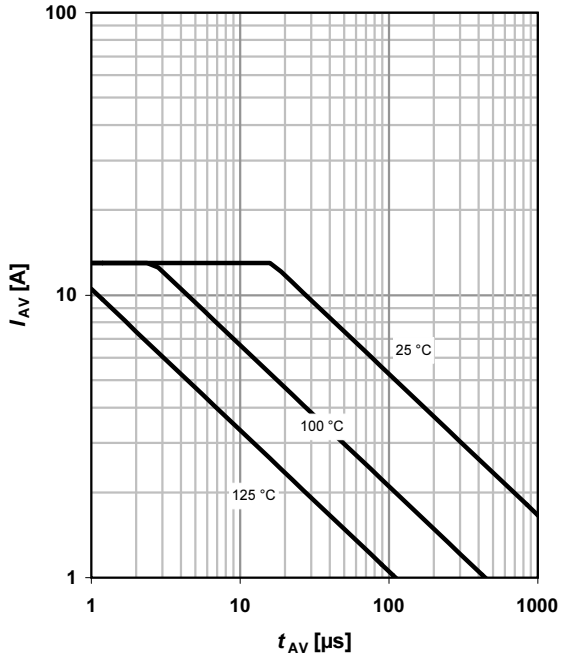
parameter: T_j



13 Avalanche characteristics

I_{AS}=f(t_{AV}); R_{GS}=25 Ω

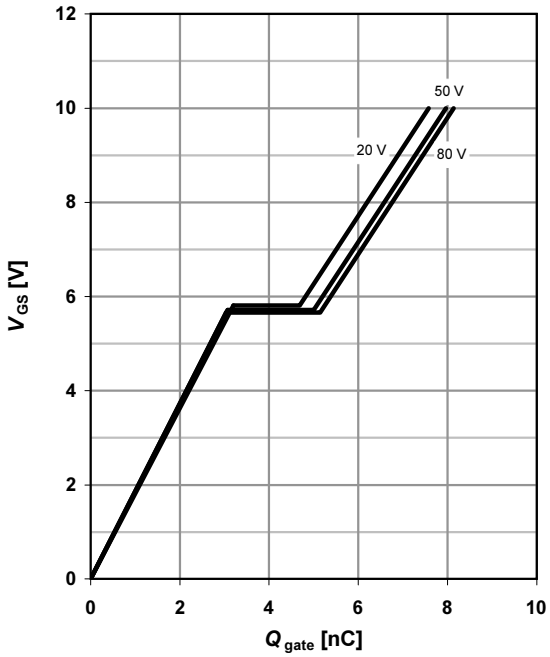
parameter: $T_{j(start)}$



14 Typ. gate charge

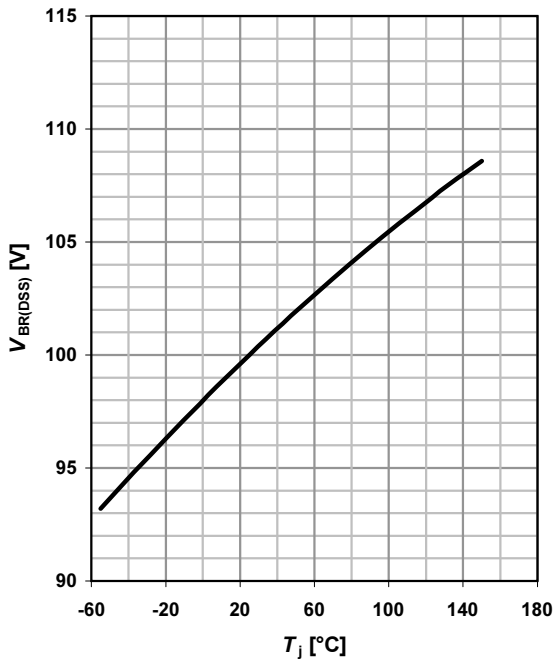
V_{GS}=f(Q_{gate}); I_D=13 A pulsed

parameter: V_{DD}

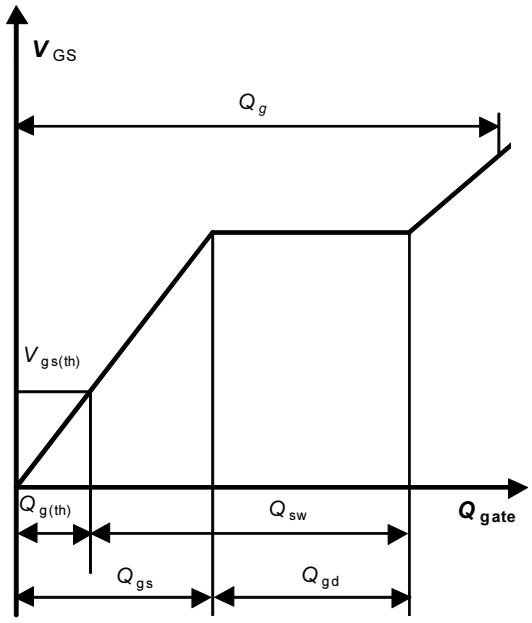


15 Drain-source breakdown voltage

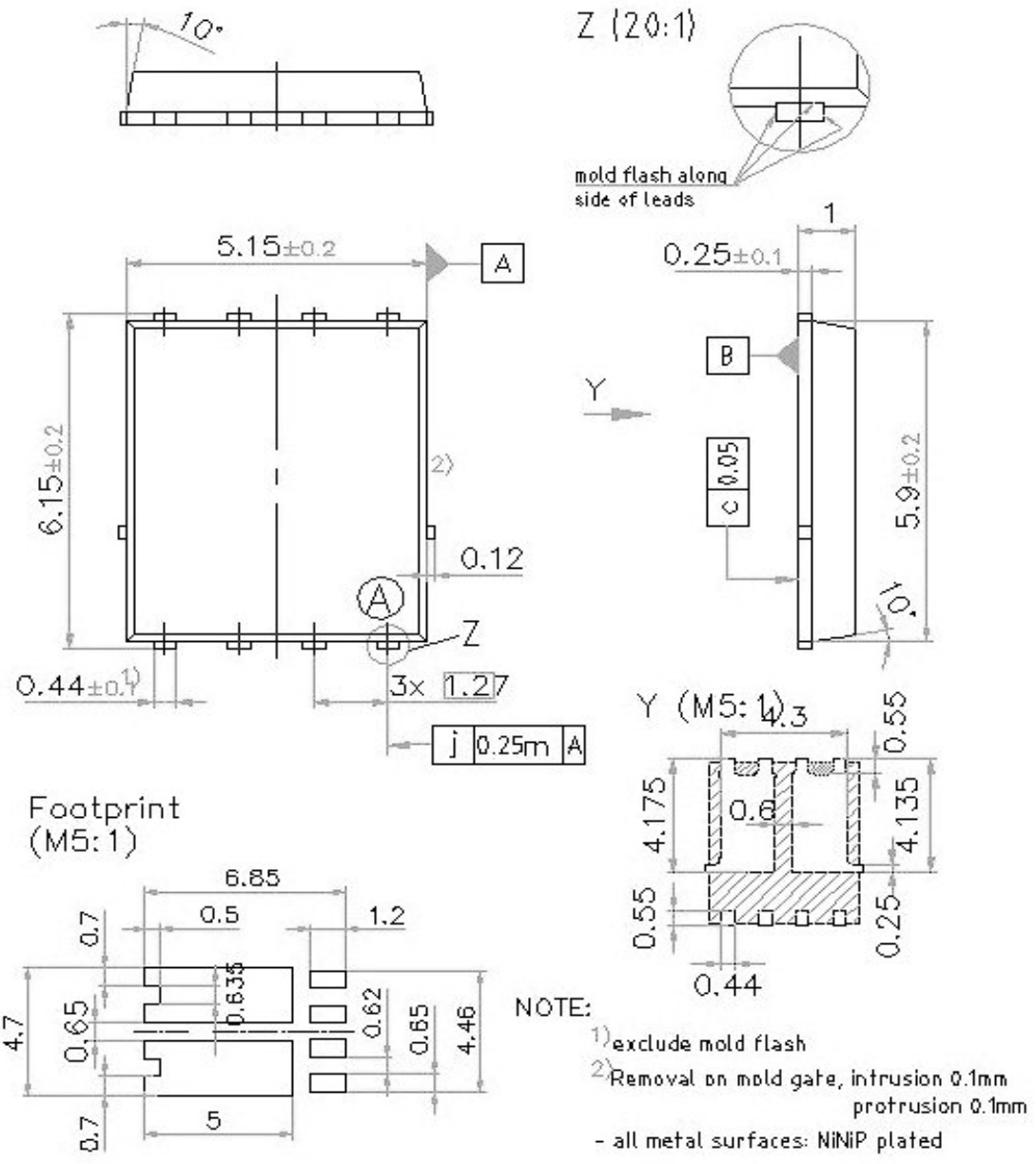
$V_{BR(DSS)}$=f(T_j); I_D=1 mA



16 Gate charge waveforms



Package Outline and Footprint **PG-TDSON-8 dual**



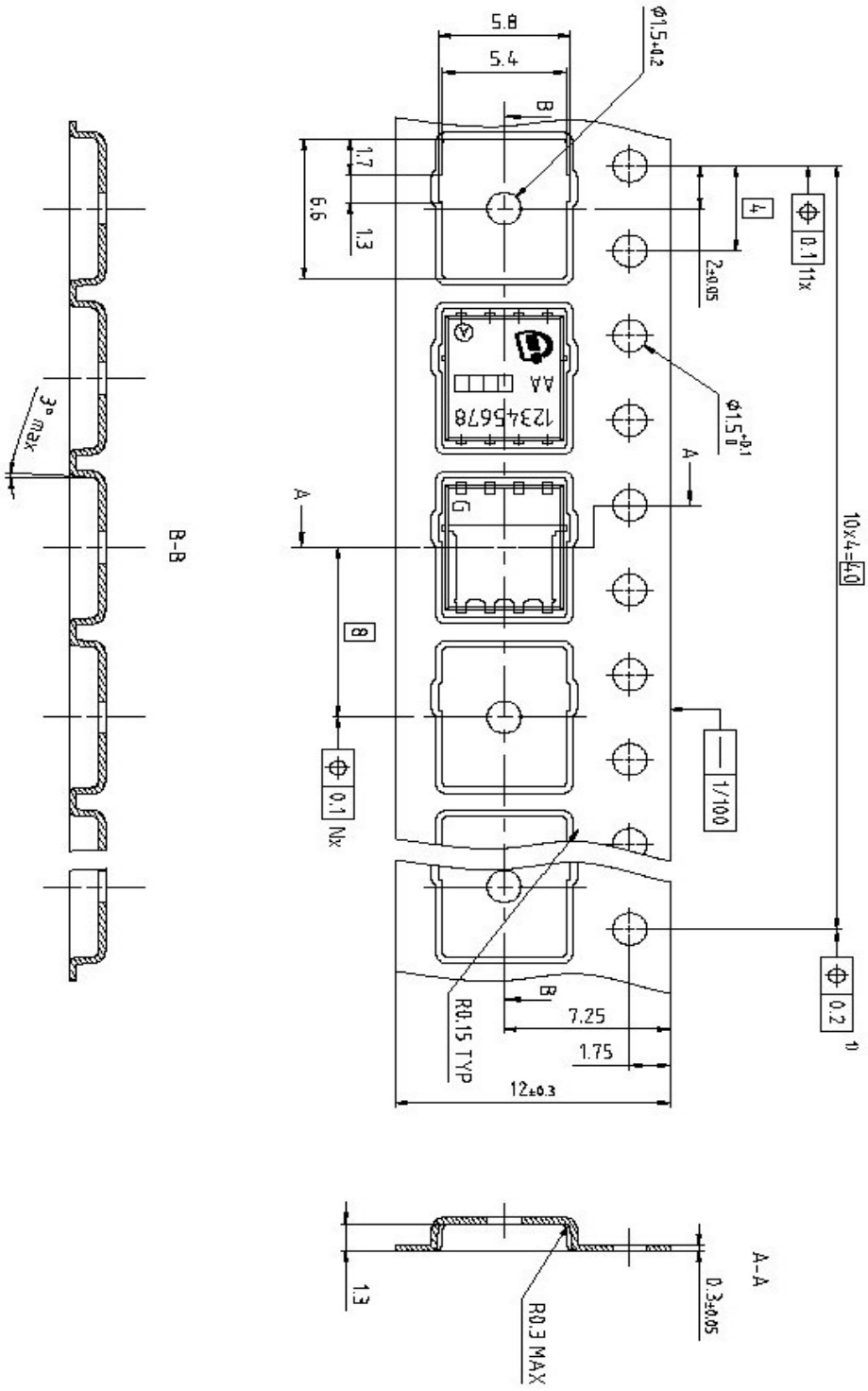
NOTE:

1) exclude mold flash

2) Removal on mold gate, intrusion 0.1mm
protrusion 0.1mm

- all metal surfaces: NiNiP plated

Tape **PG-TDSON-8**



Dimensions in mm

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